

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

# 2SA1202

POWER AMPLIFIER APPLICATIONS  
VOLTAGE AMPLIFIER APPLICATIONS

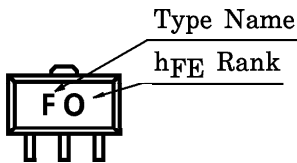
- Suitable for driver of 30~35 Watts Audio Amplifier
- $P_C=1\sim 2W$  (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SC2882

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CB0}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-400	mA
Base Current	$I_B$	-80	mA
Collector Power Dissipation	$P_C$	500	mW
Collector Power Dissipation	$P_C^*$	1000	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$

$P_C^*$  : Mounted on ceramic substrate ( $250mm^2 \times 0.8t$ )

Marking

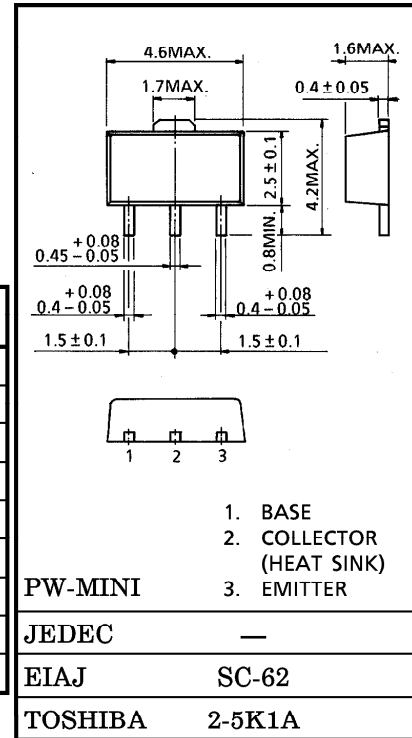


ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -80V, I_E = 0$	—	—	-0.1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-80	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -2V, I_C = -50mA$	70	—	240	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -200mA$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -200mA, I_B = -20mA$	—	—	-0.4	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -2V, I_C = -5mA$	-0.55	—	-0.8	V
Transition Frequency	$f_T$	$V_{CE} = -10V, I_C = -10mA$	—	120	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	14	—	pF

Note :  $h_{FE}$  Classification O : 70~140, Y : 120~240

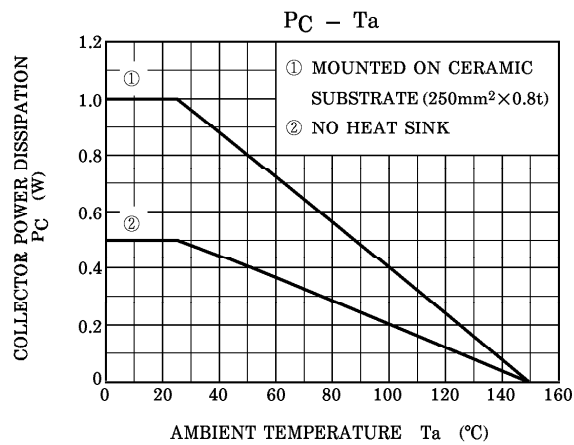
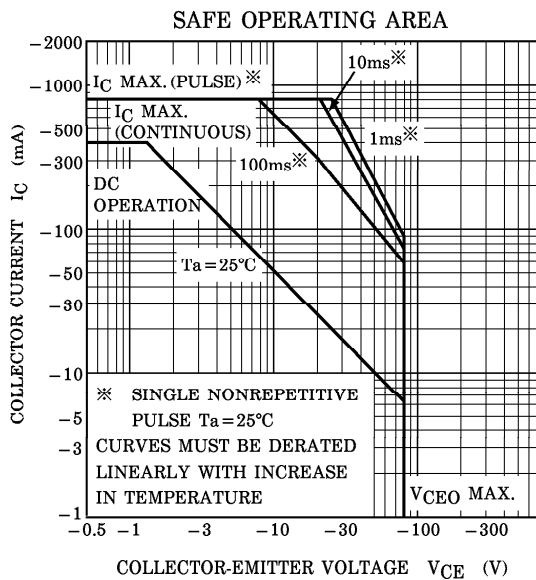
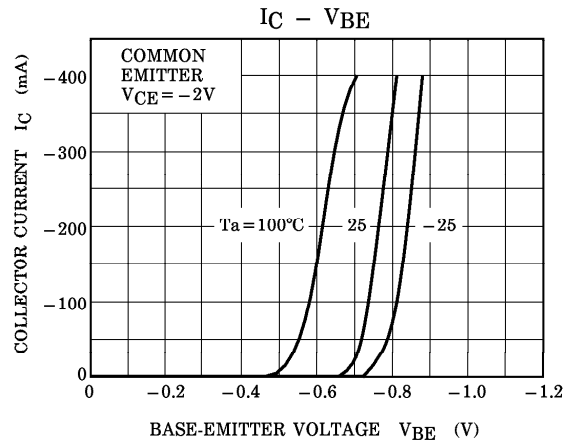
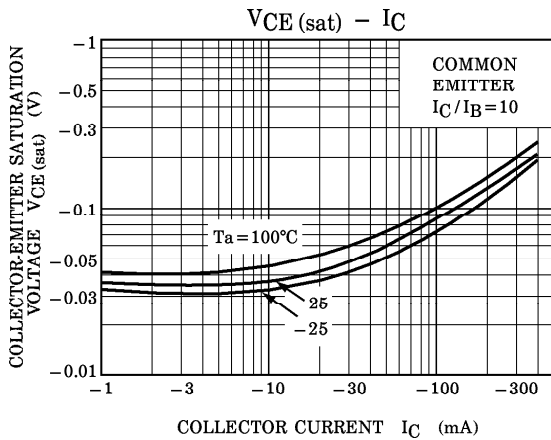
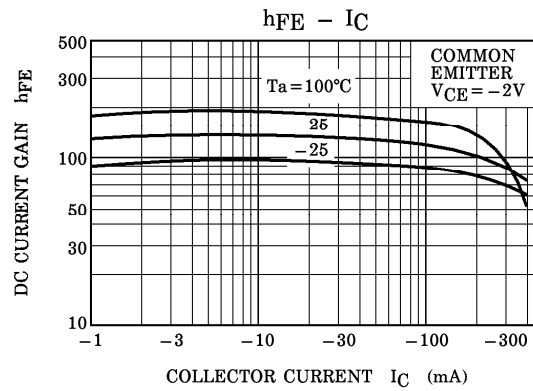
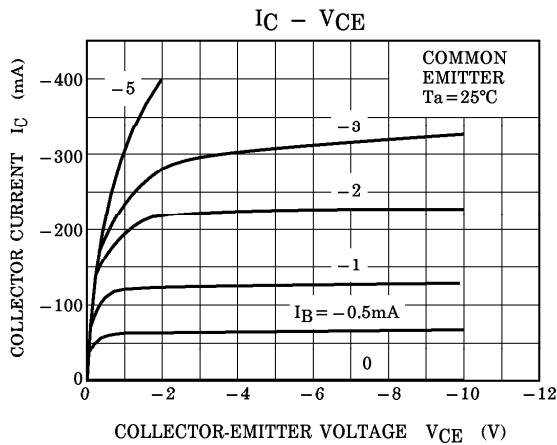
Unit in mm



Weight : 0.05g

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